

TENTATIVE

Features and Applications

- Low ON-state resistance.
- Very high speed switching.
- Low voltage drive.

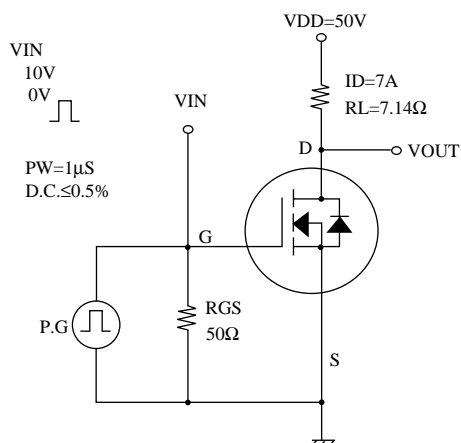
Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	VDSS	100	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID peak PW≤10μS, dutycycle≤1%	15	A
Drain Current (Pulse)	IDP (Tc=25°C)	60	A
Allowable power Dissipation	PD	60	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

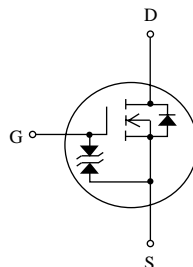
Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA , VGS=0	100			V
Gate to Source Breakdown Voltage	V(BR)GSS	IG=±100μA , VDS=0	±20			V
Zero Gate Voltage Drain Current	IDSS	VDS=100V , VGS=0			100	μA
Gate to Source Leakage Current	IGSS	VGS=±100V , VDS=0			±10	μA
Cutoff Voltage	VGS(Off)	VDS=16V , ID=1mA	1.0		2.0	V
Forward Transfer Admittance	yfs	VDS=10V , ID=7A	7	11.5		S
Static Drain to Source on State Resistance	RDS(On)	ID=7A , VGS=10V		100	135	mΩ
	RDS(On)	ID=7A , VGS=4V		135	180	mΩ
Input Capacitance	Ciss	VDS=20V , f=1MHz		1230		pF
Output Capacitance	Coss	VDS=20V , f=1MHz		200		pF
Reverse Transfer Capacitance	Crss	VDS=20V , f=1MHz		40		pF
Turn-ON Delay Time	td(On)	See Specified Test Circuit		14		ns
Rise Time	tr			21		ns
Turn-oFF Delay Time	td(Off)			230		ns
Fall Time	tf			90		ns
Diode Forward Voltage	VSD	IS=15A , VGS=0		1.0	1.5	V

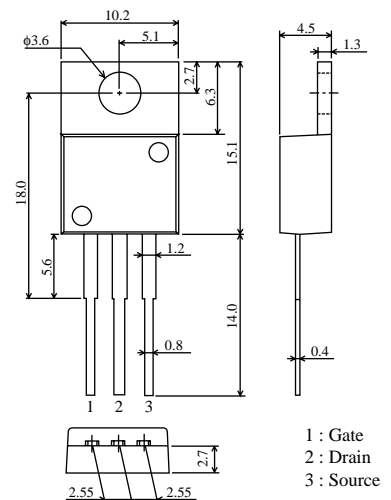
Switching Time Test Circuit



Electrical Connection



Case Outline TO-220(unit:mm)



Specifications and information herein are subject to change without notice.

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